

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,087,535 B2
APPLICATION NO. : 10/676169
DATED : August 8, 2006
INVENTOR(S) : Garo J. Derderian et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page Item (56), References Cited, FOREIGN PATENT DOCUMENTS,
Replace "EP 0794588 10/1997"
With --EP 0794568 10/1997--

Title Page, Item (56)
Page 2, OTHER PUBLICATIONS, please delete:
"U.S. Appl. No. 09/843,004, filed Aug. 2000, Mercaldi"

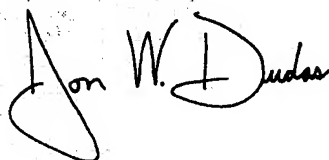
Column 6, line 49
Replace "chlorosilanes (SiHCl₃, SiH₂Cl₂, and SiH₃Cl) and methysi"
With --chlorosilanes (SiHCl₃, SiH₂Cl₂, and SiH₃Cl) and methylsi--

Column 7, line 64
Replace "conductive material 38 may comprise a storage node within"
With --conductive material 38 which may comprise a storage node within--

Column 8, claim 8, line 49
Replace "The deposition method of claim is 1, further comprising"
With --The deposition method of claim 1, further comprising--

Signed and Sealed this

Fifteenth Day of May, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office